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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	8375
Number of Logic Elements/Cells	67000
Total RAM Bits	4526080
Number of I/O	490
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (Tj)
Package / Case	1156-BBGA
Supplier Device Package	1156-FPBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-70ea-8lfn1156i

Figure 2-4. General Purpose PLL Diagram

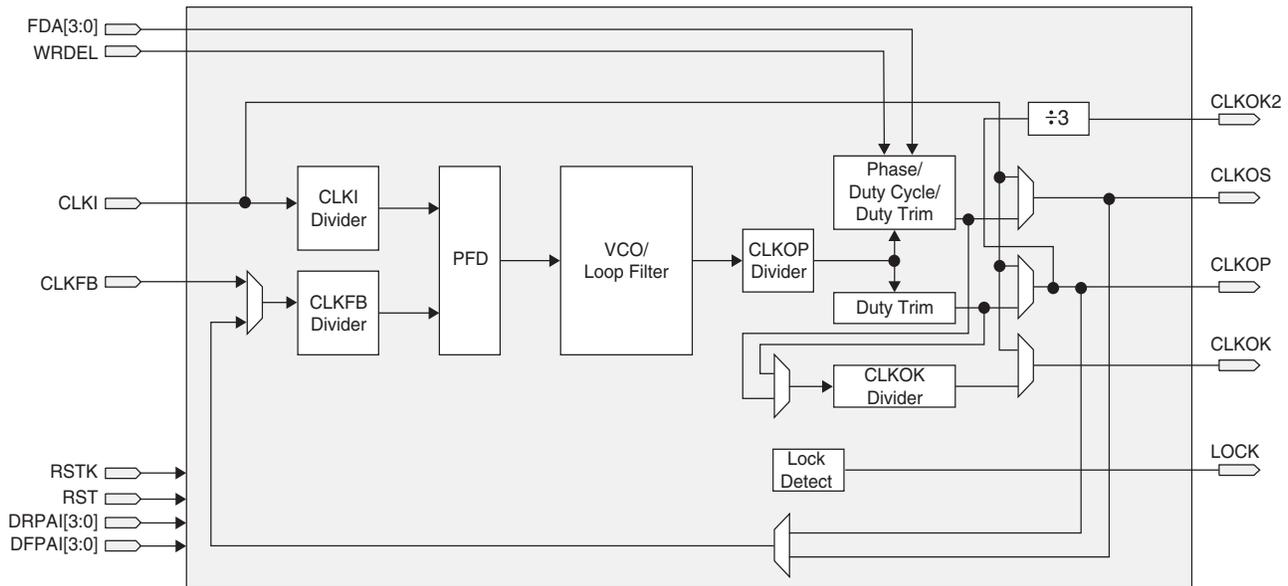


Table 2-4 provides a description of the signals in the PLL blocks.

Table 2-4. PLL Blocks Signal Descriptions

Signal	I/O	Description
CLKI	I	Clock input from external pin or routing
CLKFB	I	PLL feedback input from CLKOP, CLKOS, or from a user clock (pin or logic)
RST	I	"1" to reset PLL counters, VCO, charge pumps and M-dividers
RSTK	I	"1" to reset K-divider
WRDEL	I	DPA Fine Delay Adjust input
CLKOS	O	PLL output to clock tree (phase shifted/duty cycle changed)
CLKOP	O	PLL output to clock tree (no phase shift)
CLKKOK	O	PLL output to clock tree through secondary clock divider
CLKKOK2	O	PLL output to clock tree (CLKOP divided by 3)
LOCK	O	"1" indicates PLL LOCK to CLKI
FDA [3:0]	I	Dynamic fine delay adjustment on CLKOS output
DRPAI[3:0]	I	Dynamic coarse phase shift, rising edge setting
DFPAI[3:0]	I	Dynamic coarse phase shift, falling edge setting

Delay Locked Loops (DLL)

In addition to PLLs, the LatticeECP3 family of devices has two DLLs per device.

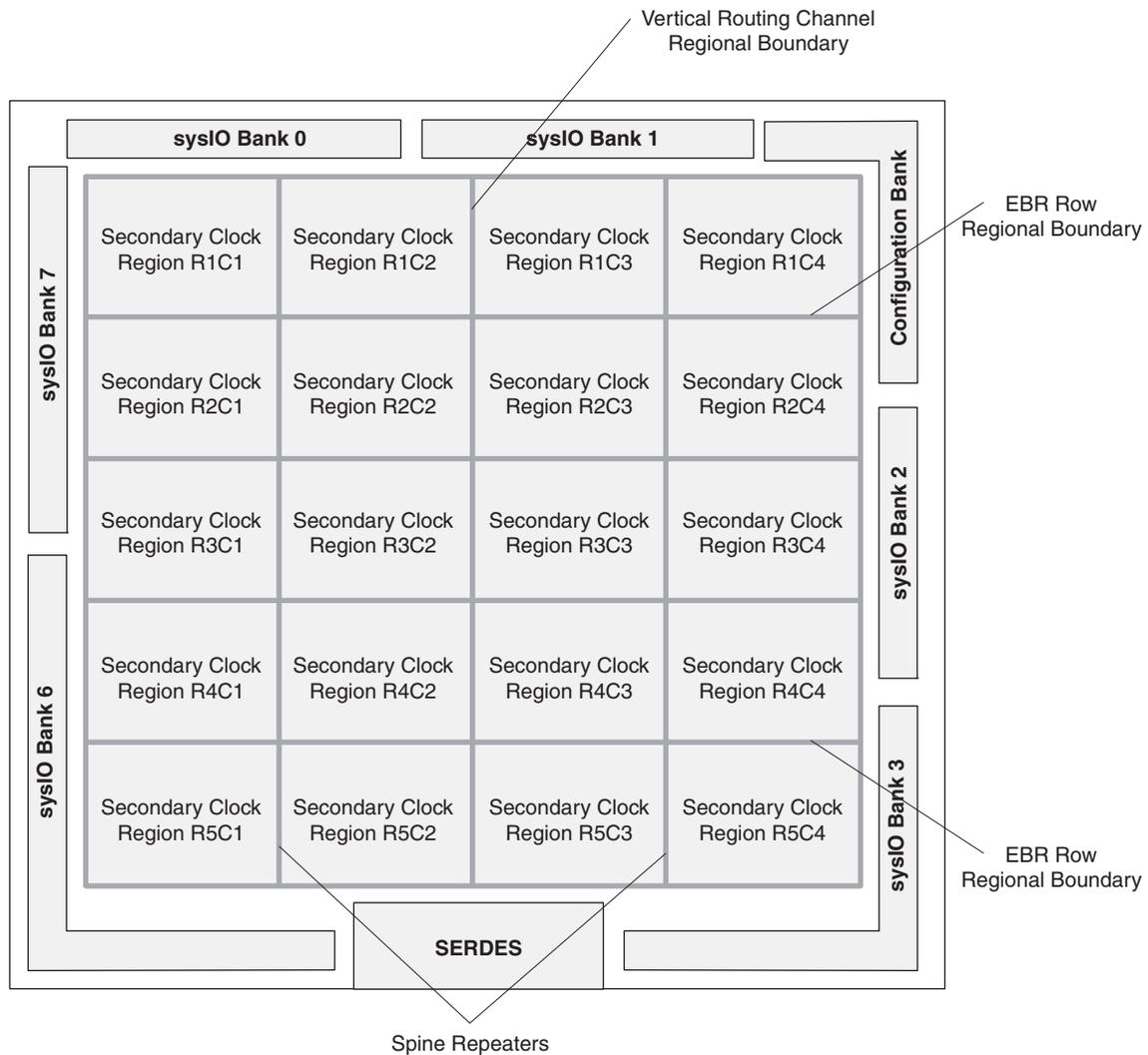
CLKI is the input frequency (generated either from the pin or routing) for the DLL. CLKI feeds into the output muxes block to bypass the DLL, directly to the DELAY CHAIN block and (directly or through divider circuit) to the reference input of the Phase Detector (PD) input mux. The reference signal for the PD can also be generated from the Delay Chain signals. The feedback input to the PD is generated from the CLKFB pin or from a tapped signal from the Delay chain.

The PD produces a binary number proportional to the phase and frequency difference between the reference and feedback signals. Based on these inputs, the ALU determines the correct digital control codes to send to the delay

Table 2-6. Secondary Clock Regions

Device	Number of Secondary Clock Regions
ECP3-17	16
ECP3-35	16
ECP3-70	20
ECP3-95	20
ECP3-150	36

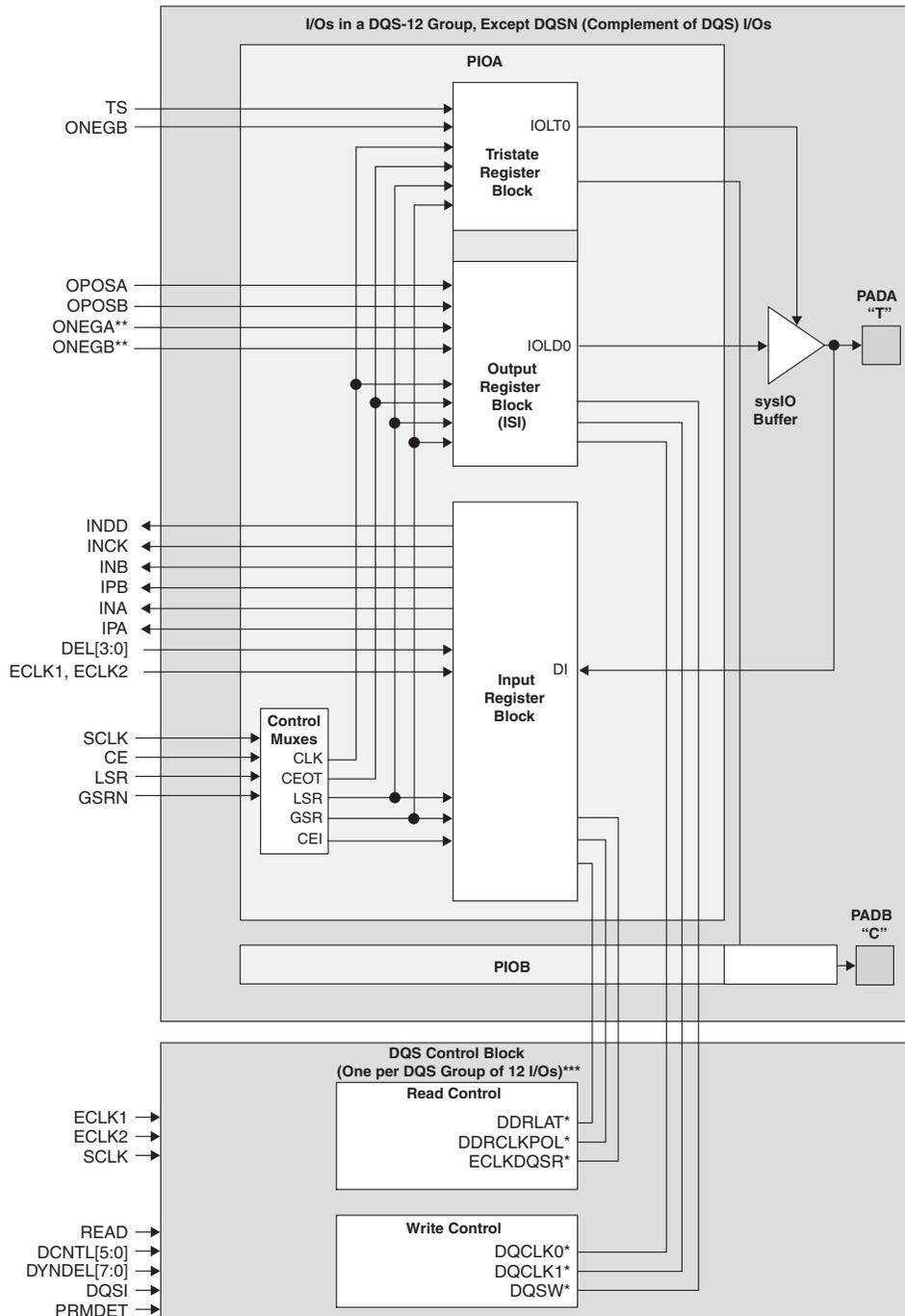
Figure 2-15. LatticeECP3-70 and LatticeECP3-95 Secondary Clock Regions



Programmable I/O Cells (PIC)

Each PIC contains two PIOs connected to their respective sysI/O buffers as shown in Figure 2-32. The PIO Block supplies the output data (DO) and the tri-state control signal (TO) to the sysI/O buffer and receives input from the buffer. Table 2-11 provides the PIO signal list.

Figure 2-32. PIC Diagram



* Signals are available on left/right/top edges only.
** Signals are available on the left and right sides only
*** Selected PIO.

Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as “T” and “C”) as shown in Figure 2-32. The PAD Labels “T” and “C” distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as LVDS inputs.

Table 2-11. PIO Signal List

Name	Type	Description
INDD	Input Data	Register bypassed input. This is not the same port as INCK.
IPA, INA, IPB, INB	Input Data	Ports to core for input data
OPOSA, ONEGA ¹ , OPOSB, ONEGB ¹	Output Data	Output signals from core. An exception is the ONEGB port, used for tristate logic at the DQS pad.
CE	PIO Control	Clock enables for input and output block flip-flops.
SCLK	PIO Control	System Clock (PCLK) for input and output/TS blocks. Connected from clock ISB.
LSR	PIO Control	Local Set/Reset
ECLK1, ECLK2	PIO Control	Edge clock sources. Entire PIO selects one of two sources using mux.
ECLKDQSR ¹	Read Control	From DQS_STROBE, shifted strobe for memory interfaces only.
DDRCLKPOL ¹	Read Control	Ensures transfer from DQS domain to SCLK domain.
DDRLAT ¹	Read Control	Used to guarantee INDDR2 gearing by selectively enabling a D-Flip-Flop in datapath.
DEL[3:0]	Read Control	Dynamic input delay control bits.
INCK	To Clock Distribution and PLL	PIO treated as clock PIO, path to distribute to primary clocks and PLL.
TS	Tristate Data	Tristate signal from core (SDR)
DQCLK0 ¹ , DQCLK1 ¹	Write Control	Two clocks edges, 90 degrees out of phase, used in output gearing.
DQSW ²	Write Control	Used for output and tristate logic at DQS only.
DYNDEL[7:0]	Write Control	Shifting of write clocks for specific DQS group, using 6:0 each step is approximately 25ps, 128 steps. Bit 7 is an invert (timing depends on input frequency). There is also a static control for this 8-bit setting, enabled with a memory cell.
DCNTL[6:0]	PIO Control	Original delay code from DDR DLL
DATAVALID ¹	Output Data	Status flag from DATAVALID logic, used to indicate when input data is captured in IOLOGIC and valid to core.
READ	For DQS_Strobe	Read signal for DDR memory interface
DQSI	For DQS_Strobe	Unshifted DQS strobe from input pad
PRMBDET	For DQS_Strobe	DQSI biased to go high when DQSI is tristate, goes to input logic block as well as core logic.
GSRN	Control from routing	Global Set/Reset

1. Signals available on left/right/top edges only.

2. Selected PIO.

PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Input Register Block

The input register blocks for the PIOs, in the left, right and top edges, contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-33 shows the input register block for the left, right and top edges. The input register block for the bottom edge contains one element to register the input signal and no DDR registers. The following description applies to the input register block for PIOs in the left, right and top edges only.

Input signals are fed from the sysI/O buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In single data rate (SDR) the data is registered with the system clock by one of the registers in the single data rate sync register block.

In DDR mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (ECLKDQSR) in the DDR Memory mode or ECLK signal when using DDR Generic mode, creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

A gearbox function can be implemented in each of the input registers on the left and right sides. The gearbox function takes a double data rate signal applied to PIOA and converts it as four data streams, INA, IPA, INB and IPB. The two data streams from the first set of DDR registers are synchronized to the edge clock and then to the system clock before entering the core. Figure 2-30 provides further information on the use of the gearbox function.

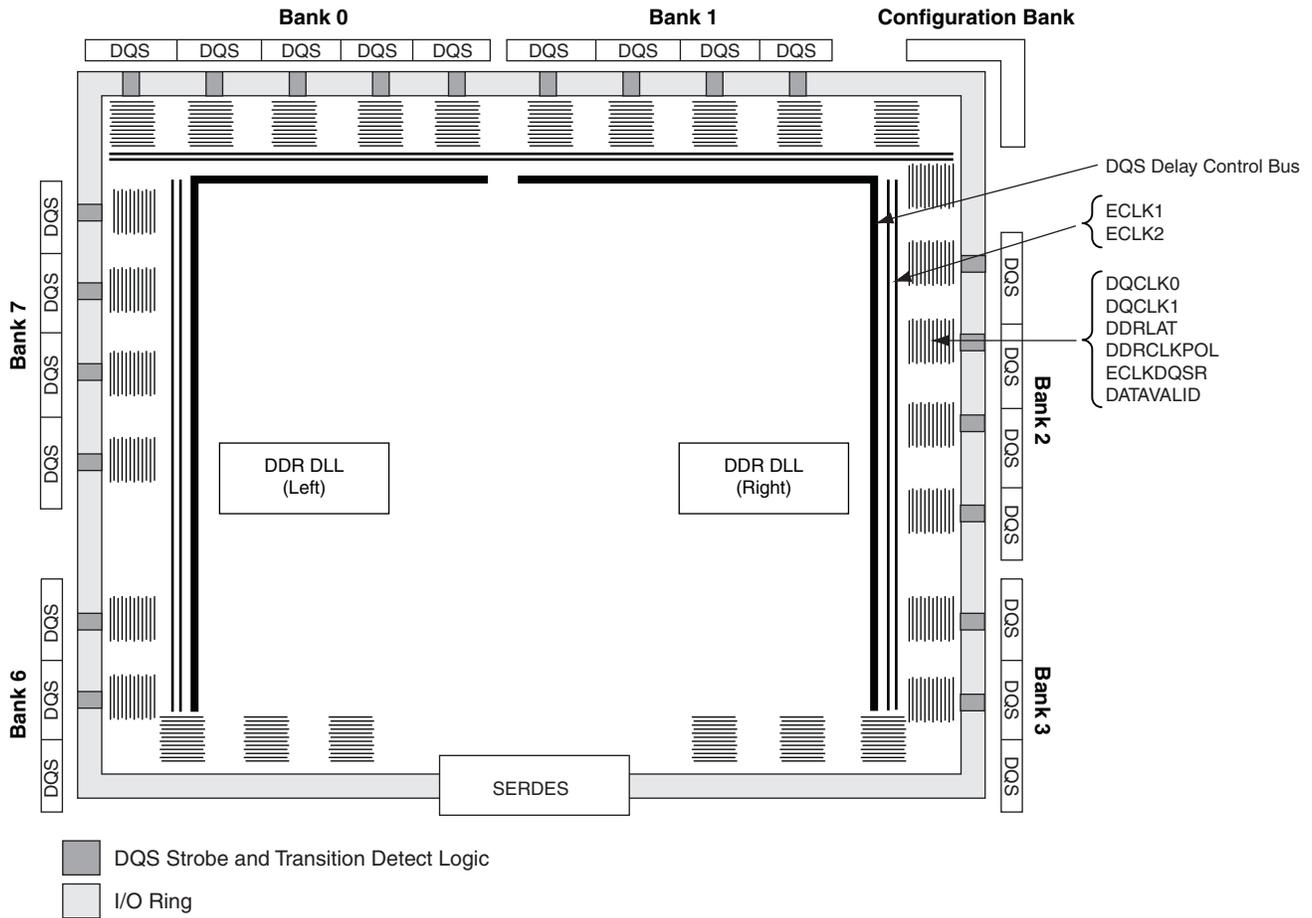
The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the ECLKDQSR (DDR Memory Interface mode) or ECLK (DDR Generic mode). The DDRLAT signal is used to ensure the data transfer from the synchronization registers to the clock transfer and gearbox registers.

The ECLKDQSR, DDRCLKPOL and DDRLAT signals are generated in the DQS Read Control Logic Block. See Figure 2-37 for an overview of the DQS read control logic.

Further discussion about using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.

Please see TN1180, [LatticeECP3 High-Speed I/O Interface](#) for more information on this topic.

Figure 2-36. Edge Clock, DLL Calibration and DQS Local Bus Distribution



*Includes shared configuration I/Os and dedicated configuration I/Os.

To accomplish write leveling in DDR3, each DQS group has a slightly different delay that is set by DYN DELAY[7:0] in the DQS Write Control logic block. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock.

LatticeECP3 input and output registers can also support DDR gearing that is used to receive and transmit the high speed DDR data from and to the DDR3 Memory.

LatticeECP3 supports the 1.5V SSTL I/O standard required for the DDR3 memory interface. For more information, refer to the sysIO section of this data sheet.

Please see TN1180, [LatticeECP3 High-Speed I/O Interface](#) for more information on DDR Memory interface implementation in LatticeECP3.

sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, BLVDS, HSTL, SSTL Class I & II, LVCMOS, LVTTL, LVPECL, PCI.

sysI/O Buffer Banks

LatticeECP3 devices have six sysI/O buffer banks: six banks for user I/Os arranged two per side. The banks on the bottom side are wraparounds of the banks on the lower right and left sides. The seventh sysI/O buffer bank (Configuration Bank) is located adjacent to Bank 2 and has dedicated/shared I/Os for configuration. When a shared pin is not used for configuration it is available as a user I/O. Each bank is capable of supporting multiple I/O standards. Each sysI/O bank has its own I/O supply voltage (V_{CCIO}). In addition, each bank, except the Configuration Bank, has voltage references, V_{REF1} and V_{REF2} , which allow it to be completely independent from the others. Figure 2-38 shows the seven banks and their associated supplies.

In LatticeECP3 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO} . LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO} .

Each bank can support up to two separate V_{REF} voltages, V_{REF1} and V_{REF2} , that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

Enhanced Configuration Options

LatticeECP3 devices have enhanced configuration features such as: decryption support, TransFR™ I/O and dual-boot image support.

1. TransFR (Transparent Field Reconfiguration)

TransFR I/O (TFR) is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a single ispVM command. TransFR I/O allows I/O states to be frozen during device configuration. This allows the device to be field updated with a minimum of system disruption and downtime. See TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) for details.

2. Dual-Boot Image Support

Dual-boot images are supported for applications requiring reliable remote updates of configuration data for the system FPGA. After the system is running with a basic configuration, a new boot image can be downloaded remotely and stored in a separate location in the configuration storage device. Any time after the update the LatticeECP3 can be re-booted from this new configuration file. If there is a problem, such as corrupt data during download or incorrect version number with this new boot image, the LatticeECP3 device can revert back to the original backup golden configuration and try again. This all can be done without power cycling the system. For more information, please see TN1169, [LatticeECP3 sysCONFIG Usage Guide](#).

Soft Error Detect (SED) Support

LatticeECP3 devices have dedicated logic to perform Cycle Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, the LatticeECP3 device can also be programmed to utilize a Soft Error Detect (SED) mode that checks for soft errors in configuration SRAM. The SED operation can be run in the background during user mode. If a soft error occurs, during user mode (normal operation) the device can be programmed to generate an error signal.

For further information on SED support, please see TN1184, [LatticeECP3 Soft Error Detection \(SED\) Usage Guide](#).

External Resistor

LatticeECP3 devices require a single external, 10 kOhm $\pm 1\%$ value between the XRES pin and ground. Device configuration will not be completed if this resistor is missing. There is no boundary scan register on the external resistor pad.

On-Chip Oscillator

Every LatticeECP3 device has an internal CMOS oscillator which is used to derive a Master Clock (MCCLK) for configuration. The oscillator and the MCCLK run continuously and are available to user logic after configuration is completed. The software default value of the MCCLK is nominally 2.5 MHz. Table 2-16 lists all the available MCCLK frequencies. When a different Master Clock is selected during the design process, the following sequence takes place:

1. Device powers up with a nominal Master Clock frequency of 3.1 MHz.
2. During configuration, users select a different master clock frequency.
3. The Master Clock frequency changes to the selected frequency once the clock configuration bits are received.
4. If the user does not select a master clock frequency, then the configuration bitstream defaults to the MCCLK frequency of 2.5 MHz.

This internal 130 MHz $\pm 15\%$ CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1169, [LatticeECP3 sysCONFIG Usage Guide](#).

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$I_{IL}, I_{IH}^{1,4}$	Input or I/O Low Leakage	$0 \leq V_{IN} \leq (V_{CCIO} - 0.2 \text{ V})$	—	—	10	μA
$I_{IH}^{1,3}$	Input or I/O High Leakage	$(V_{CCIO} - 0.2 \text{ V}) < V_{IN} \leq 3.6 \text{ V}$	—	—	150	μA
I_{PU}	I/O Active Pull-up Current	$0 \leq V_{IN} \leq 0.7 V_{CCIO}$	-30	—	-210	μA
I_{PD}	I/O Active Pull-down Current	$V_{IL} (\text{MAX}) \leq V_{IN} \leq V_{CCIO}$	30	—	210	μA
I_{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL} (\text{MAX})$	30	—	—	μA
I_{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μA
I_{BHLO}	Bus Hold Low Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	210	μA
I_{BHHO}	Bus Hold High Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	-210	μA
V_{BHT}	Bus Hold Trip Points	$0 \leq V_{IN} \leq V_{IH} (\text{MAX})$	$V_{IL} (\text{MAX})$	—	$V_{IH} (\text{MIN})$	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}, 1.5 \text{ V}, 1.2 \text{ V},$ $V_{CC} = 1.2 \text{ V}, V_{IO} = 0 \text{ to } V_{IH} (\text{MAX})$	—	5	8	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}, 1.5 \text{ V}, 1.2 \text{ V},$ $V_{CC} = 1.2 \text{ V}, V_{IO} = 0 \text{ to } V_{IH} (\text{MAX})$	—	5	7	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. T_A 25 °C, $f = 1.0 \text{ MHz}$.

3. Applicable to general purpose I/Os in top and bottom banks.

4. When used as V_{REF} maximum leakage = 25 μA .

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

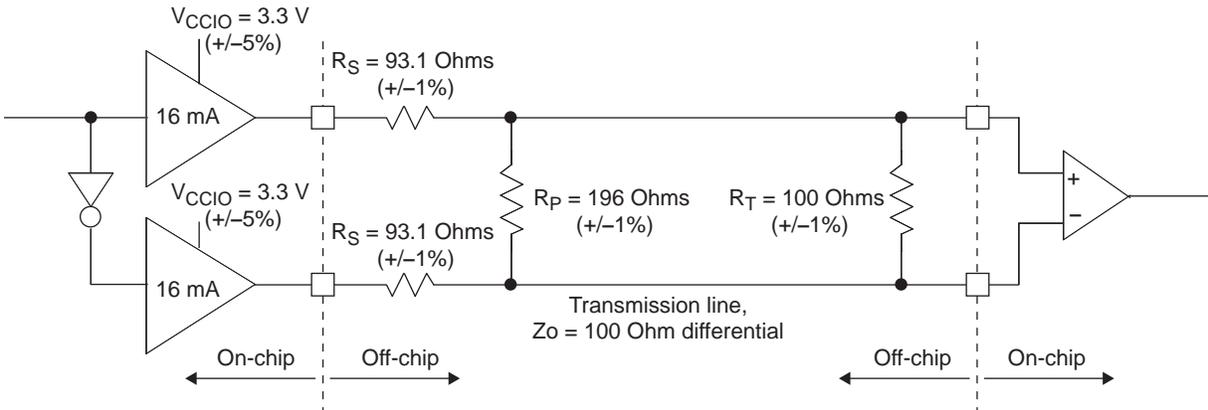


Table 3-3. LVPECL33 DC Conditions¹

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply ($\pm 5\%$)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor ($\pm 1\%$)	93	Ω
R_P	Driver Parallel Resistor ($\pm 1\%$)	196	Ω
R_T	Receiver Termination ($\pm 1\%$)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Clock	Min.	Typ.	Max.	Units	
f _{IN}	Input clock frequency (CLKI, CLKFB)		Edge clock	2	—	500	MHz	
			Primary clock ⁴	2	—	420	MHz	
f _{OUT}	Output clock frequency (CLKOP, CLKOS)		Edge clock	4	—	500	MHz	
			Primary clock ⁴	4	—	420	MHz	
f _{OUT1}	K-Divider output frequency	CLKOK		0.03125	—	250	MHz	
f _{OUT2}	K2-Divider output frequency	CLKOK2		0.667	—	166	MHz	
f _{VCO}	PLL VCO frequency			500	—	1000	MHz	
f _{PDF} ³	Phase detector input frequency		Edge clock	2	—	500	MHz	
			Primary clock ⁴	2	—	420	MHz	
AC Characteristics								
t _{PA}	Programmable delay unit			65	130	260	ps	
t _{DT}	Output clock duty cycle (CLKOS, at 50% setting)		Edge clock	45	50	55	%	
			f _{OUT} ≤ 250 MHz	Primary clock	45	50	55	%
			f _{OUT} > 250 MHz	Primary clock	30	50	70	%
t _{CFA}	Coarse phase shift error (CLKOS, at all settings)			-5	0	+5	% of period	
t _{OPW}	Output clock pulse width high or low (CLKOS)			1.8	—	—	ns	
t _{OPJIT} ¹	Output clock period jitter	f _{OUT} ≥ 420 MHz		—	—	200	ps	
		420 MHz > f _{OUT} ≥ 100 MHz		—	—	250	ps	
		f _{OUT} < 100 MHz		—	—	0.025	UIPP	
t _{SK}	Input clock to output clock skew when N/M = integer			—	—	500	ps	
t _{LOCK} ²	Lock time	2 to 25 MHz		—	—	200	us	
		25 to 500 MHz		—	—	50	us	
t _{UNLOCK}	Reset to PLL unlock time to ensure fast reset			—	—	50	ns	
t _{HI}	Input clock high time	90% to 90%		0.5	—	—	ns	
t _{LO}	Input clock low time	10% to 10%		0.5	—	—	ns	
t _{IPJIT}	Input clock period jitter			—	—	400	ps	
t _{RST}	Reset signal pulse width high, RSTK			10	—	—	ns	
	Reset signal pulse width high, RST			500	—	—	ns	

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for f_{PDF} > 4 MHz. For f_{PDF} < 4 MHz, the jitter numbers may not be met in certain conditions. Please contact the factory for f_{PDF} < 4 MHz.
4. When using internal feedback, maximum can be up to 500 MHz.

DLL Timing

Over Recommended Operating Conditions

Parameter	Description	Condition	Min.	Typ.	Max.	Units
f_{REF}	Input reference clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{FB}	Feedback clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{CLKOP}^1	Output clock frequency, CLKOP		133	—	500	MHz
f_{CLKOS}^2	Output clock frequency, CLKOS		33.3	—	500	MHz
t_{PJIT}	Output clock period jitter (clean input)			—	200	ps p-p
t_{DUTY}	Output clock duty cycle (at 50% levels, 50% duty cycle input clock, 50% duty cycle circuit turned off, time reference delay mode)	Edge Clock	40		60	%
		Primary Clock	30		70	%
$t_{DUTYTRD}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, time reference delay mode)	Primary Clock < 250 MHz	45		55	%
		Primary Clock \geq 250 MHz	30		70	%
		Edge Clock	45		55	%
$t_{DUTYCIR}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, clock injection removal mode) with DLL cascading	Primary Clock < 250 MHz	40		60	%
		Primary Clock \geq 250 MHz	30		70	%
		Edge Clock	45		55	%
t_{SKEW}^3	Output clock to clock skew between two outputs with the same phase setting		—	—	100	ps
t_{PHASE}	Phase error measured at device pads between off-chip reference clock and feedback clocks		—	—	+/-400	ps
t_{PWH}	Input clock minimum pulse width high (at 80% level)		550	—	—	ps
t_{PWL}	Input clock minimum pulse width low (at 20% level)		550	—	—	ps
t_{INSTB}	Input clock period jitter		—	—	500	ps
t_{LOCK}	DLL lock time		8	—	8200	cycles
t_{RSWD}	Digital reset minimum pulse width (at 80% level)		3	—	—	ns
t_{DEL}	Delay step size		27	45	70	ps
t_{RANGE1}	Max. delay setting for single delay block (64 taps)		1.9	3.1	4.4	ns
t_{RANGE4}	Max. delay setting for four chained delay blocks		7.6	12.4	17.6	ns

1. CLKOP runs at the same frequency as the input clock.

2. CLKOS minimum frequency is obtained with divide by 4.

3. This is intended to be a “path-matching” design guideline and is not a measurable specification.

PCI Express Electrical and Timing Characteristics

AC and DC Characteristics

Over Recommended Operating Conditions

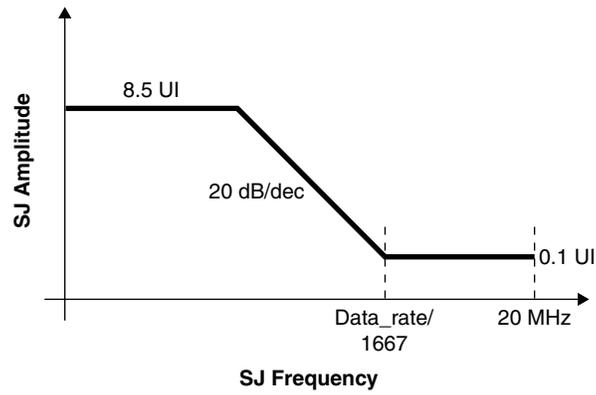
Symbol	Description	Test Conditions	Min	Typ	Max	Units
Transmit¹						
UI	Unit interval		399.88	400	400.12	ps
V _{TX-DIFF_P-P}	Differential peak-to-peak output voltage		0.8	1.0	1.2	V
V _{TX-DE-RATIO}	De-emphasis differential output voltage ratio		-3	-3.5	-4	dB
V _{TX-CM-AC_P}	RMS AC peak common-mode output voltage		—	—	20	mV
V _{TX-RCV-DETECT}	Amount of voltage change allowed during receiver detection		—	—	600	mV
V _{TX-DC-CM}	Tx DC common mode voltage		0	—	V _{CCOB} + 5%	V
I _{TX-SHORT}	Output short circuit current	V _{TX-D+} =0.0 V V _{TX-D-} =0.0 V	—	—	90	mA
Z _{TX-DIFF-DC}	Differential output impedance		80	100	120	Ohms
RL _{TX-DIFF}	Differential return loss		10	—	—	dB
RL _{TX-CM}	Common mode return loss		6.0	—	—	dB
T _{TX-RISE}	Tx output rise time	20 to 80%	0.125	—	—	UI
T _{TX-FALL}	Tx output fall time	20 to 80%	0.125	—	—	UI
L _{TX-SKEW}	Lane-to-lane static output skew for all lanes in port/link		—	—	1.3	ns
T _{TX-EYE}	Transmitter eye width		0.75	—	—	UI
T _{TX-EYE-MEDIAN-TO-MAX-JITTER}	Maximum time between jitter median and maximum deviation from median		—	—	0.125	UI
Receive^{1, 2}						
UI	Unit Interval		399.88	400	400.12	ps
V _{RX-DIFF_P-P}	Differential peak-to-peak input voltage		0.34 ³	—	1.2	V
V _{RX-IDLE-DET-DIFF_P-P}	Idle detect threshold voltage		65	—	340 ³	mV
V _{RX-CM-AC_P}	Receiver common mode voltage for AC coupling		—	—	150	mV
Z _{RX-DIFF-DC}	DC differential input impedance		80	100	120	Ohms
Z _{RX-DC}	DC input impedance		40	50	60	Ohms
Z _{RX-HIGH-IMP-DC}	Power-down DC input impedance		200K	—	—	Ohms
RL _{RX-DIFF}	Differential return loss		10	—	—	dB
RL _{RX-CM}	Common mode return loss		6.0	—	—	dB
T _{RX-IDLE-DET-DIFF-ENTERTIME}	Maximum time required for receiver to recognize and signal an unexpected idle on link		—	—	—	ms

1. Values are measured at 2.5 Gbps.

2. Measured with external AC-coupling on the receiver.

3. Not in compliance with PCI Express 1.1 standard.

Figure 3-18. XAUI Sinusoidal Jitter Tolerance Mask



Note: The sinusoidal jitter tolerance is measured with at least 0.37 UIpp of Deterministic jitter (Dj) and the sum of Dj and Rj (random jitter) is at least 0.55 UIpp. Therefore, the sum of Dj, Rj and Sj (sinusoidal jitter) is at least 0.65 UIpp (Dj = 0.37, Rj = 0.18, Sj = 0.1).

Serial Rapid I/O Type 2/CPRI LV E.24 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}^1	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX_DIFF_DC}$	Differential impedance		80	100	120	Ohms
$J_{TX_DDJ}^{3,4,5}$	Output data deterministic jitter		—	—	0.17	UI
$J_{TX_TJ}^{2,3,4,5}$	Total output data jitter		—	—	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
$J_{RX_DJ}^{2,3,4,5}$	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
$J_{RX_RJ}^{2,3,4,5}$	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
$J_{RX_SJ}^{2,3,4,5}$	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
$J_{RX_TJ}^{1,2,3,4,5}$	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-19. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR _{SDO}	Serial data rate		270	—	2975	Mbps
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ^{1,2}	Serial output jitter, alignment	2970Mbps	—	—	0.30	UI
T _{JTIMING}	Serial output jitter, timing	270 Mbps	—	—	0.20	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mbps	—	—	1.0	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mbps	—	—	2.0	UI

Notes:

1. Timing jitter is measured in accordance with SMPTE RP 184-1996, SMPTE RP 192-1996 and the applicable serial data transmission standard, SMPTE 259M-1997 or SMPTE 292M (proposed). A color bar test pattern is used. The value of f_{CLK} is 270 MHz or 360 MHz for SMPTE 259M, 540 MHz for SMPTE 344M or 1485 MHz for SMPTE 292M serial data rates. See the Timing Jitter Bandpass section.
2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
3. All Tx jitter is measured at the output of an industry standard cable driver; connection to the cable driver is via a 50 Ohm impedance differential signal from the Lattice SERDES device.
4. The cable driver drives: RL=75 Ohm, AC-coupled at 270, 1485, or 2970 Mbps, RREFLVL=RREFPRE=4.75 kOhm 1%.

Table 3-20. Receive

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR _{SDI}	Serial input data rate		270	—	2970	Mbps
CID	Stream of non-transitions (=Consecutive Identical Digits)		7(3G)/26(SMPTE Triple rates) @ 10-12 BER	—	—	Bits

Table 3-21. Reference Clock

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
F _{VCLK}	Video output clock frequency		27	—	74.25	MHz
DC _V	Duty cycle, video clock		45	50	55	%

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-17EA			ECP3-35EA		
Pin Type		256 ftBGA	328 csBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA
Emulated Differential I/O per Bank	Bank 0	13	10	18	13	21	24
	Bank 1	7	5	12	7	18	18
	Bank 2	2	2	4	1	8	8
	Bank 3	4	2	13	5	20	19
	Bank 6	5	1	13	6	22	20
	Bank 7	6	9	10	6	11	13
	Bank 8	12	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0
	Bank 2	2	2	3	3	6	6
	Bank 3	5	4	9	4	9	12
	Bank 6	5	4	9	4	11	12
	Bank 7	5	6	8	5	9	10
	Bank 8	0	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	26/13	20/10	36/18	26/13	42/21	48/24
	Bank 1	14/7	10/5	24/12	14/7	36/18	36/18
	Bank 2	8/4	9/4	14/7	8/4	28/14	28/14
	Bank 3	18/9	12/6	44/22	18/9	58/29	63/31
	Bank 6	20/10	11/5	44/22	20/10	67/33	65/32
	Bank 7	23/11	30/15	36/18	23/11	40/20	46/23
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank ²	Bank 0	2	1	3	2	3	4
	Bank 1	1	0	2	1	3	3
	Bank 2	0	0	1	0	2	2
	Bank 3	1	0	3	1	3	4
	Bank 6	1	0	3	1	4	4
	Bank 7	1	2	2	1	3	3
	Configuration Bank 8	0	0	0	0	0	0
SERDES Quads		1	1	1	1	1	1

1. These pins must remain floating on the board.
2. Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-70EA		
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43
	Bank 1	18	24	39
	Bank 2	8	12	13
	Bank 3	20	23	33
	Bank 6	22	25	33
	Bank 7	11	16	18
	Bank 8	12	12	12
High-Speed Differential I/O per Bank	Bank 0	0	0	0
	Bank 1	0	0	0
	Bank 2	6	9	9
	Bank 3	9	12	16
	Bank 6	11	14	16
	Bank 7	9	12	13
	Bank 8	0	0	0
Total Single-Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43
	Bank 1	36/18	48/24	78/39
	Bank 2	28/14	42/21	44/22
	Bank 3	58/29	71/35	98/49
	Bank 6	67/33	78/39	98/49
	Bank 7	40/20	56/28	62/31
	Bank 8	24/12	24/12	24/12
DDR Groups Bonded per Bank ¹	Bank 0	3	5	7
	Bank 1	3	4	7
	Bank 2	2	3	3
	Bank 3	3	4	5
	Bank 6	4	4	5
	Bank 7	3	4	4
	Configuration Bank 8	0	0	0
SERDES Quads		1	2	3

1. Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.

Date	Version	Section	Change Summary
			LatticeECP3 Maximum I/O Buffer Speed table – Description column, references to VCCIO = 3.0V changed to 3.3V.
			Updated SERDES External Reference Clock Waveforms.
			Transmitter and Receiver Latency Block Diagram – Updated sections of the diagram to match descriptions on the SERDES/PCS Latency Break-down table.
		Pinout Information	“Logic Signal Connections” section heading renamed “Package Pinout Information”. Software menu selections within this section have been updated.
			Signal Descriptions table – Updated description for V _{CCA} signal.
April 2012	02.2EA	Architecture	Updated first paragraph of Output Register Block section.
			Updated the information about sysIO buffer pairs below Figure 2-38.
			Updated the information relating to migration between devices in the Density Shifting section.
		DC and Switching Characteristics	Corrected the Definitions in the sysCLOCK PLL Timing table for t _{RST} .
		Ordering Information	Updated topside marks with new logos in the Ordering Information section.
February 2012	02.1EA	All	Updated document with new corporate logo.
November 2011	02.0EA	Introduction	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		Architecture	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		DC and Switching Characteristics	Updated LatticeECP3 Supply Current table power numbers.
			Typical Building Block Function Performance table, LatticeECP3 External Switching Characteristics table, LatticeECP3 Internal Switching Characteristics table and LatticeECP3 Family Timing Adders: Added speed grade -9 and updated speed grade -8, -7 and -6 timing numbers.
		Pinout Information	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		Ordering Information	Added information for LatticeECP3-17EA, 328-ball csBGA package.
Added ordering information for low power devices and -9 speed grade devices.			
July 2011	01.9EA	DC and Switching Characteristics	Removed ESD Performance table and added reference to LatticeECP3 Product Family Qualification Summary document.
			sysCLOCK PLL Timing table, added footnote 4.
			External Reference Clock Specification table – removed reference to VREF-CM-AC and removed footnote for VREF-CM-AC.
		Pinout Information	Pin Information Summary table: Corrected VCCIO Bank8 data for LatticeECP3-17EA 256-ball ftBGA package and LatticeECP3-35EA 256-ball ftBGA package.
April 2011	01.8EA	Architecture	Updated Secondary Clock/Control Sources text section.
		DC and Switching Characteristics	Added data for 150 Mbps to SERDES Power Supply Requirements table.
			Updated Frequencies in Table 3-6 Serial Output Timing and Levels
			Added Data for 150 Mbps to Table 3-7 Channel Output Jitter
			Corrected External Switching Characteristics table, Description for DDR3 Clock Timing, t _{JIT} .
			Corrected Internal Switching Characteristics table, Description for EBR Timing, t _{SUWREN_EBR} and t _{HWREN_EBR} .
			Added footnote 1 to sysConfig Port Timing Specifications table.
Updated description for RX-CIDs to 150M in Table 3-9 Serial Input Data Specifications			

Date	Version	Section	Change Summary
			Updated Simplified Channel Block Diagram for SERDES/PCS Block diagram.
		Updated Device Configuration text section.	
		Corrected software default value of MCCLK to be 2.5 MHz.	
		DC and Switching Characteristics	Updated VCCOB Min/Max data in Recommended Operating Conditions table.
		Corrected footnote 2 in sysIO Recommended Operating Conditions table.	
		Added added footnote 7 for $t_{\text{SKEW_PRIB}}$ to External Switching Characteristics table.	
		Added 2-to-1 Gearing text section and table.	
		Updated External Reference Clock Specification (refclkp/refclkn) table.	
		LatticeECP3 sysCONFIG Port Timing Specifications - updated t_{DINIT} information.	
		Added sysCONFIG Port Timing waveform.	
		Serial Input Data Specifications table, delete Typ data for $V_{\text{RX-DIFF-S}}$.	
		Added footnote 4 to sysCLOCK PLL Timing table for t_{PFD} .	
		Added SERDES/PCS Block Latency Breakdown table.	
		External Reference Clock Specifications table, added footnote 4, add symbol name vREF-IN-DIFF.	
		Added SERDES External Reference Clock Waveforms.	
		Updated Serial Output Timing and Levels table.	
		Pin-to-pin performance table, changed "typically 3% slower" to "typically slower".	
		Updated timing information	
		Updated SERDES minimum frequency.	
		Added data to the following tables: External Switching Characteristics, Internal Switching Characteristics, Family Timing Adders, Maximum I/O Buffer Speed, DLL Timing, High Speed Data Transmitter, Channel Output Jitter, Typical Building Block Function Performance, Register-to-Register Performance, and Power Supply Requirements.	
Updated Serial Input Data Specifications table.			
Updated Transmit table, Serial Rapid I/O Type 2 Electrical and Timing Characteristics section.			
Pinout Information	Updated Signal Description tables.		
Updated Pin Information Summary tables and added footnote 1.			
February 2009	01.0	—	Initial release.